

Transistors	Features
$\frac{\text{SOD882}}{1 \text{SOD882}}$	Low Leakage Response Time is Typically < 1 ns ESD Rating of Class 3 per Human Body Model IEC61000-4-2 Level 4 ESD Protection These are Pb-Free Devices We declare that the material of product compliance with RoHS requirements and Halogen Free. Applications Cellular phones audio Digital cameras Portable applications Mobile telephone
Marking :5C	

Discription

The ESD8D5.0C is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, digital cameras and many other portable applications where board space is at a premium.

Device	Marking	Shipping
ESD8D5.0C	5C	10000/Tape&Reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Air discharge Contact discharge		±25 ±20	kV kV
Total Power Dissipation on FR-5 Board (Note 1)	PD	200	mW
@ T _A =25			
Junction and Storage Temperature Range	TJ,TSTG	-55 to 150	
Lead Solder Temperature – Maximum (10	TL	260	
Second Duration)			

Stresses exceeding Maximum Ratings may damage the device. Maximum Rating are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

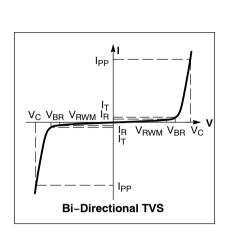
1. FR-5 = 1.0*0.75*0.62 in.



ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Symbol	Parameter			
I _{PP}	Maximum Reverse Peak Pulse Current			
V _C	Clamping Voltage @ IPP			
V _{RWM}	Working Peak Reverse Voltage			
I _R	Maximum Reverse Leakage Current @ $\mathrm{V}_{\mathrm{RWM}}$			
V _{BR}	Breakdown Voltage @ I _T			
Ι _Τ	Test Current			
P _{pk}	Peak Power Dissipation			
С	Capacitance @ $V_R = 0$ and f = 1.0 MHz			



ELECTRICAL CHARACTERISTICS

	V _{RWM} (V)	I _{R1} (μΑ) @ V _{RWM}	I _{R2} (μA) @ V _R =3.5∨	V _{BR} (V) @ म (Note 2)		ŀт	V _C (V) @ I _{PP} = 1 A (Note 3)	V _C (V) @MAX I _{PP} (Note 3)	I _{PF} (A) (Note 3)	Р_{РК}(W) (Note 3)	C (pF)
Device	Max	Max	Мах	Min	Max	mA	Max	Max	Max	Max	Max
ESD8D5.0C	5.0	0.5	0.3	5.6	8.0	1.0	9.8	12.5	5.5	69	15

Other voltage available upon request.

2. V_{BR} is measured with a pulse test current IT at an ambient temperature of 25

3. Surge current waveform per Figure 3.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS(CURVES)



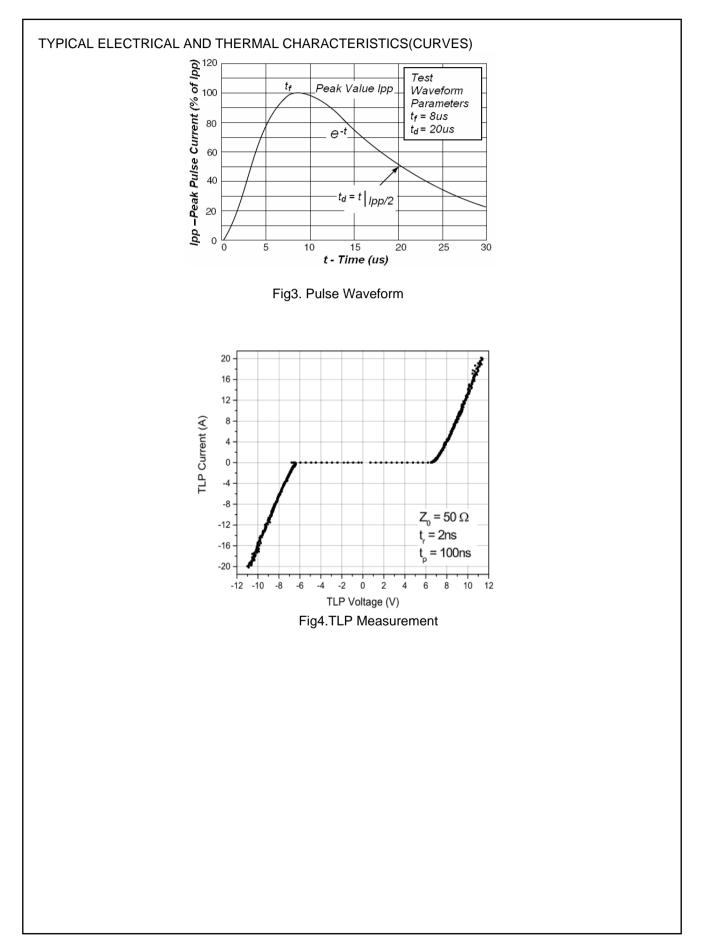
Fig1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000-4-2



Fig2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2



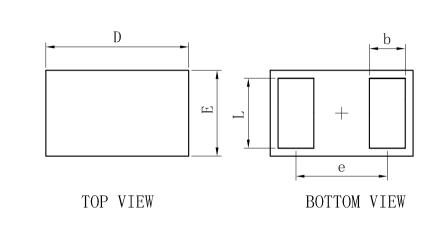




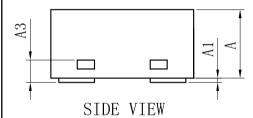




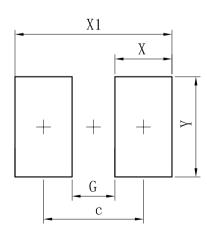
OUTLINE AND DIMENSIONS



S0D882					
Dim	Min	Тур	Max		
D	0.95	1.00	1.05		
E	0.55	0.60	0.65		
е	-	0.64	-		
L	0.44	0.49	0.54		
b	0.20	0.25	0.30		
А	0.43	0.48	0.53		
A1	0	_	0.05		
A3	0.127REF.				
All Dimensions in mm					



SOLDERING FOOTPRINT



Dimensions	(mm)
С	0.70
G	0.30
Х	0.40
X1	1.10
Y	0.70

单击下面可查看定价,库存,交付和生命周期等信息

>>DIOS(迪恩思)